

ABSTRACT

WAFER PROCESSING METHOD

A wafer processing method for dividing a wafer into individual device chips is disclosed. The wafer is formed from an SiC substrate having a first surface and a second surface. The wafer processing method includes a separation start point forming step of setting the focal point of a laser beam having a transmission wavelength to the SiC substrate inside the SiC substrate at a predetermined depth from the first surface or the second surface, and next applying the laser beam to the first surface or the second surface as relatively moving the focal point and the SiC substrate to thereby form a modified layer parallel to the first surface and cracks extending from the modified layer along a c-plane, thus forming a separation start point, and a wafer separating step of applying an external force to the wafer, thereby separating the wafer into a first wafer having the first surface and a second wafer having the second surface at the separation start point.

(Figure 7)